



Shanghai Lunsure Electronic
Technology Co.,Ltd
Tel:0086-21-37185008
Fax:0086-21-57152769

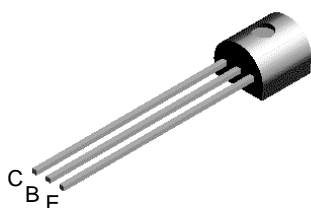
S8050

**NPN Silicon
Transistors**

Features

- TO-92 Plastic-Encapsulate Transistors
- Capable of 0.625Watts($T_{amb}=25^{\circ}C$) of Power Dissipation.
- Collector-current 0.5A
- Collector-base Voltage 40V
- Operating and storage junction temperature range: $-55^{\circ}C$ to $+150^{\circ}C$
- Marking Code: S8050

Pin Configuration



Electrical Characteristics @ $25^{\circ}C$ Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
--------	-----------	-----	-----	-------

OFF CHARACTERISTICS

$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=100\mu A$, $I_E=0$)	40	---	Vdc
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=0.1mA$, $I_B=0$)	25	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_E=100\mu A$, $I_C=0$)	5.0	---	Vdc
I_{CBO}	Collector Cutoff Current ($V_{CB}=40Vdc$, $I_E=0$)	---	0.1	μA
I_{CEO}	Collector Cutoff Current ($V_{CE}=20Vdc$, $I_B=0$)	---	0.1	μA
I_{EBO}	Emitter Cutoff Current ($V_{EB}=3.0Vdc$, $I_C=0$)	---	0.1	μA

ON CHARACTERISTICS

$h_{FE(1)}$	DC Current Gain ($I_C=50mA$, $V_{CE}=1.0Vdc$)	85	300	---
$h_{FE(2)}$	DC Current Gain ($I_C=500mA$, $V_{CE}=1.0Vdc$)	50	---	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=500mA$, $I_B=50mA$)	---	0.6	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C=500mA$, $I_B=50mA$)	---	1.2	Vdc
V_{EB}	Base- Emitter Voltage ($I_E=100mA$)	---	1.4	Vdc

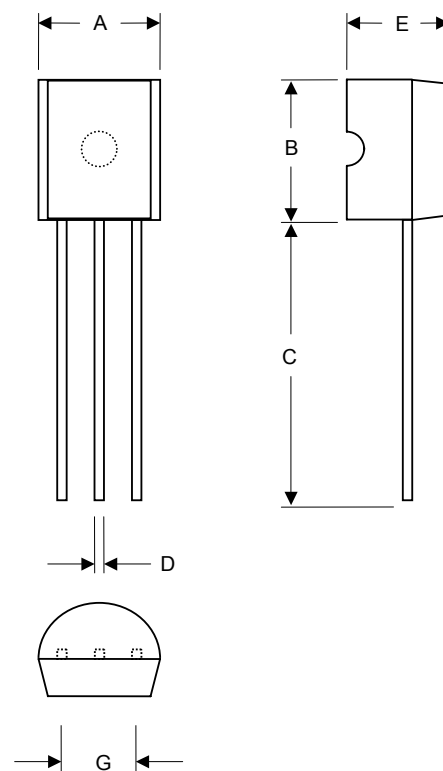
SMALL-SIGNAL CHARACTERISTICS

f_T	Transistor Frequency ($I_C=20mA$, $V_{CE}=6.0Vdc$, $f=30MHz$)	150	---	MHz
-------	--	-----	-----	-----

CLASSIFICATION OF $h_{FE(1)}$

Rank	C	D
Range	120-200	160-300

TO-92



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.170	.190	4.33	4.83	
B	.170	.190	4.30	4.83	
C	.550	.590	13.97	14.97	
D	.010	.020	0.36	0.56	
E	.130	.160	3.30	3.96	
G	.010	.104	2.44	2.64	